

3 FILES SEARCHED...

6 FILES SEARCHED...

L2 401 L1 AND (SURFACE OR SUBSTRATE)

=> s 12 and (melt or heat) (p) distortion

L3 6 L2 AND (MELT OR HEAT) (P) DISTORTION

=> s (12 or 13) and (Antibacterial or microbiocid? or antimicrobial or silver)

L4 77 (L2 OR L3) AND (ANTIBACTERIAL OR MICROBIOCID? OR ANTIMICROBIAL OR SILVER)

=> s (11 or 12 or 13 or 14) and bath(4p) (pH or basic or caustic)

L5 28 (L1 OR L2 OR L3 OR L4) AND BATH(4P) (PH OR BASIC OR CAUSTIC)

=> s (11-15) and Klebsiella

L6 0 ((L1 OR L2 OR L3 OR L4 OR L5)) AND KLEBSIELLA

=> s (11 or 12) and klebsiella

L7 0 (L1 OR L2) AND KLEBSIELLA

=> s (11-5) and modified plate

4 FILES SEARCHED...

L8 0 ((L1 OR L2 OR L3 OR L4 OR L5)) AND MODIFIED PLATE

=> dup rem 15

PROCESSING COMPLETED FOR L5

L9 28 DUP REM L5 (0 DUPLICATES REMOVED)

=> d 13 1-6

L3 ANSWER 1 OF 6 USPATFULL

AN 2002:256840 USPATFULL

TI Lamp utilizing fiber for enhanced starting field

IN Golkowski, Czeslaw, Ithaca, NY, UNITED STATES
 Hammer, David, Ithaca, NY, UNITED STATES
 Song, Byungmoo, Ithaca, NY, UNITED STATES
 Tian, Yonglai, Fairfax, VA, UNITED STATES
 Cekic, Miodrag, Bethesda, MD, UNITED STATES
 Ury, Michael G., Great Barrington, MA, UNITED STATES
 Kirkpatrick, Douglas A., Great Falls, VA, UNITED STATES

PI US 2002140381 A1 20021003

AI US 2001-838234 A1 20010420 (9)

PRAI US 2000-199810P 20000426 (60)

DT Utility

FS APPLICATION

LN.CNT 1083

INCL INCLM: 315/363.000

NCL NCLM: 315/363.000

IC [7]
 ICM: H05B041-16

L3 ANSWER 2 OF 6 USPATFULL

AN 93:65190 USPATFULL

TI Process for producing a minute-patterned **substrate**

IN Matsuno, Yoshihiro, Tsukuba, Japan
 Matsuda, Atsunori, Tsukuba, Japan
 Katayama, Shinya, Tsukuba, Japan

PA Nippon Sheet Glass Co., Ltd., Osaka, Japan (non-U.S. corporation)

PI US 5234717 19930810

AI US 1992-963035 19921019 (7)

RLI Continuation of Ser. No. US 1991-713799, filed on 12 Jun 1991, now abandoned

PRAI JP 1990-156482 19900614
DT Utility
FS Granted
LN.CNT 785
INCL INCLM: 427/277.000
INCLS: 427/162.000; 427/278.000; 427/294.000; 427/359.000; 427/385.500
NCL NCLM: 427/277.000
NCLS: 427/162.000; 427/278.000; 427/294.000; 427/359.000; 427/385.500
IC [5]
ICM: B05D005-00
EXF 427/162; 427/164; 427/165; 427/294; 427/296; 427/385.5; 427/355;
427/277; 427/278; 427/258; 427/359; 427/370; 427/371
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L3 ANSWER 3 OF 6 USPATFULL
AN 93:24745 USPATFULL
TI Process for making sol-gel deposited ferroelectric thin films
insensitive to their **substrates**
IN Swartz, Scott L., Dublin, OH, United States
Melling, Peter J., Worthington, OH, United States
PA Battelle Memorial Institute, Columbus, OH, United States (U.S.
corporation)
PI US 5198269 19930330
AI US 1989-399724 19890828 (7)
RLI Continuation-in-part of Ser. No. US 1989-342272, filed on 24 Apr 1989,
now abandoned
DT Utility
FS Granted
LN.CNT 1323
INCL INCLM: 427/226.000
INCLS: 427/126.200; 427/126.300; 427/419.300; 427/419.200; 427/379.000;
427/380.000
NCL NCLM: 427/226.000
NCLS: 427/126.200; 427/126.300; 427/379.000; 427/380.000; 427/419.200;
427/419.300
IC [5]
ICM: B05D003-02
EXF 427/419.3; 427/126.2; 427/126.3; 427/100; 427/62; 427/63; 427/226;
427/419.2; 427/379; 427/380; 505/734; 505/735
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L3 ANSWER 4 OF 6 EUROPATFULL COPYRIGHT 2003 WILA

PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET

AN 764992 EUROPATFULL ED 19970421 EW 199713 FS OS
TIEN Thin piezoelectric film element, process for the preparation thereof and
ink jet recording head using thin piezoelectric film element.
TIDE Piezoelektrisches Duennschichtelement, Verfahren zum Herstellen und
dieses piezoelektrische Duennschichtelement verwendender
Tintenstrahldruckkopf.
TIFR Element a couche mince piezoelectrique, procede de fabrication, et tete
d'enregistrement a jet d'encre utilisant cet element a couche mince
piezoelectrique.
IN Shimada, Masato, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
Nagano, JP;
Takahashi, Tetsushi, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
Nagano, JP;
Kamei, Hiroyuki, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
Nagano, JP;
Qui, Hong, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi, Nagano, JP
PA SEIKO EPSON CORPORATION, 4-1, Nishishinjuku 2-chome, Shinjuku-ku Tokyo,

JP
 SO Wila-EPZ-1997-H13-T2b
 DS R DE; R FR; R GB; R IT
 PIT EPA1 EUROPÄISCHE PATENTANMELDUNG
 PI EP 764992 A1 19970326
 OD 19970326
 AI EP 1996-114974 19960918
 PRAI JP 1995-240372 19950919
 JP 1995-322670 19951212
 JP 1996-190848 19960719
 JP 1996-245353 19960917
 IC ICM H01L041-09
 ICS H01L041-24 B41J002-045

GRANTED PATENT - ERTEILTES PATENT - BREVET DELIVRE

AN 764992 EUROPATFULL UP 20000903 EW 200034 FS PS
 TIEN Thin piezoelectric film element, process for the preparation thereof and
 ink jet recording head using thin piezoelectric film element.
 TIDE Piezoelektrisches Duennschichtelement, Verfahren zum Herstellen und
 dieses piezoelektrisches Duennschichtelement verwendender
 Tintenstrahldruckkopf.
 TIFR Element a couche mince piezoelectrique, procede de fabrication, et tete
 d'enregistrement a jet d'encre utilisant cet element a couche mince
 piezoelectrique.
 IN Shimada, Masato, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
 Nagano, JP;
 Takahashi, Tetsushi, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
 Nagano, JP;
 Kamei, Hiroyuki, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
 Nagano, JP;
 Qui, Hong, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi, Nagano, JP
 PA SEIKO EPSON CORPORATION, 4-1, Nishishinjuku 2-chome, Shinjuku-ku Tokyo,
 JP
 SO Wila-EPS-2000-H34-T2
 DS R DE; R FR; R GB; R IT
 PIT EPB1 EUROPÄISCHE PATENTSCHRIFT
 PI EP 764992 B1 20000823
 OD 19970326
 AI EP 1996-114974 19960918
 PRAI JP 1995-240372 19950919
 JP 1995-322670 19951212
 JP 1996-190848 19960719
 JP 1996-245353 19960917
 REP EP 656665 A US 5198269 A
 REN VASSANT KUMAR ET AL.: "Lead zirconate titanate films by rapid thermal
 processing", APPLIED PHYSICS LETTERS,, 18. March 1991, vol. 58, no. 11,
 pages 1161 to 1163
 IC ICM H01L041-09
 ICS H01L041-24 B41J002-045

L3 ANSWER 5 OF 6 EUROPATFULL COPYRIGHT 2003 WILA

PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET

AN 659910 EUROPATFULL ED 19991205 EW 199526 FS OS STA B
 TIEN Semiconductor device and method of fabricating the same.
 TIDE Halbleiter-Vorrichtung und Verfahren zu deren Herstellung.
 TIFR Dispositif semi-conducteur et procede pour fabriquer celui-ci.
 IN Shiindo, Masahiro, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
 Suita-shi, Osaka-fu, JP;
 Kosaka, Daisuke, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,

Suita-shi, Osaka-fu, JP;
Hikawa, Tetsuo, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
Suita-shi, Osaka-fu, JP;
Takata, Akira, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
Suita-shi, Osaka-fu, JP;
Ukai, Yukihiro, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
Suita-shi, Osaka-fu, JP;
Sawada, Takashi, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
Suita-shi, Osaka-fu, JP;
Asakawa, Toshifumi, 6-9-25, Tsukimino, Yamatoshi, Kanagawa, JP
PA MEGA CHIPS CORPORATION, 1-12-38, Esaka-cho, Suita-shi, Osaka-fu, JP;
Crystal Device Corporation, 15-16, Machikaneyama-cho, Toyonaka-shi,
Osaka-fu, JP
SO Wila-EPZ-1995-H26-T1a
DS R DE; R FR; R GB; R NL
PIT EPA2 EUROPÄISCHE PATENTANMELDUNG
PI EP 659910 A2 19950628
OD 19950628
AI EP 1994-118223 19941118
PRAI JP 1993-314147 19931119
JP 1993-314470 19931119
JP 1993-316108 19931122
JP 1993-341322 19931210
JP 1993-345314 19931220
JP 1993-350297 19931227
JP 1993-354139 19931228
JP 1994-15505 19940209
IC ICM C30B025-00
ICS C23C016-48

L3 ANSWER 6 OF 6 EUROPATFULL COPYRIGHT 2003 WILA

PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET

AN 391226 EUROPATFULL ED 20000903 EW 199041 TS OS STA B
TIE Method for manufacturing layer-built material with silicon dioxide film
containing organic colorant and the layer-built material manufactured
thereby.
TIDE Verfahren zur Herstellung eines schichtfoermig aufgebauten Materials mit
einem organischen Farbstoff enthaltenden Siliziumdioxidfilm sowie das
somit erzeugte Produkt.
TIFR Procédé pour la préparation d'un matériel stratifié avec un film de
silice contenant un colorant organique et le matériel stratifié ainsi
produit.
IN Takemura, Kazuo, 12-18, Nogami 6-chome, Takarazuka-shi, Hyogo-ken, JP;
Ino, Juichi, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP;
Kawahara, Hideo, 8-2-312 Makiochi 5-chome, Mino-shi, Osaka-fu, JP;
Kitaoka, Masaki, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken,
JP
PA NIPPON SHEET GLASS CO. LTD., 5-11, Dosho-machi 3-chome, Chuo-ku
Osaka-shi Osaka, JP
SO Wila-EPZ-1990-H41-T1
DS R DE; R FR; R GB; R IT; R NL
PIT EPA1 EUROPÄISCHE PATENTANMELDUNG
PI EP 391226 A1 19901010
OD 19901010
AI EP 1990-105873 19900328
PRAI JP 1989-83816 19890401
JP 1989-167366 19890629
JP 1989-167367 19890629
JP 1989-167368 19890629
JP 1989-204214 19890807

	JP 1989-217124	19890823		
	JP 1989-218054	19890824		
	JP 1989-229694	19890905		
	JP 1989-238295	19890913		
	JP 1989-238296	19890913		
IC	ICM C03C017-25			
	ICS C03C017-36	G02B001-10	H01J001-64	H01J029-22
	C09D001-04			

GRANTED PATENT - ERTEILTES PATENT - BREVET DELIVRE

AN	391226 EUROPATFULL UP 20011005 EW 199428 FS PS STA B			
TIEN	Method for manufacturing layer-built material with silicon dioxide film containing organic colorant and the layer-built material manufactured thereby.			
TIDE	Verfahren zur Herstellung eines schichtfoermig aufgebauten Materials mit einem organischen Farbstoff enthaltenden Siliziumdioxidfilm sowie das somit erzeugte Produkt.			
TIFR	Procede pour la preparation d'un materiel stratifie avec un film de silice contenant un colorant organique et le materiel stratifie ainsi produit.			
IN	Takemura, Kazuo, 12-18, Nogami 6-chome, Takarazuka-shi, Hyogo-ken, JP; Ino, Jyuichi, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP; Kawahara, Hideo, 8-2-312 Makiochi 5-chome, Mino-shi, Osaka-fu, JP; Kitaoka, Masaki, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP			
PA	NIPPON SHEET GLASS CO. LTD., 5-11, Doshomachi 3-chome, Chuo-ku Osaka-shi Osaka-fu, JP			
SO	Wila-EPS-1994-H28-T1			
DS	R DE; R FR; R GB; R IT; R NL			
PIT	EPB1 EUROPAEISCHE PATENTTSCHRIFT			
PI	EP 391226	B1	19940713	
OD			19901010	
AI	EP 1990-105873		19900328	
PRAI	JP 1989-83816		19890401	
	JP 1989-167366		19890629	
	JP 1989-167367		19890629	
	JP 1989-167368		19890629	
	JP 1989-204214		19890807	
	JP 1989-217124		19890823	
	JP 1989-218054		19890824	
	JP 1989-229694		19890905	
	JP 1989-238295		19890913	
	JP 1989-238296		19890913	
REP	GB 626810 A	GB	2018621 A	
REN	D. AVNIR, V. KAUFMAN and R. REISFELD, J. Noncryst. Solids 74 (1985), 395 - 406. T. TANI, Ceramics 21 (1986), No. 2, 111 - 118. PATENT ABSTRACTS OF JAPAN, unexamined applications, C field, vol. 11, no. 141, May 8, 1987 THE PATENT OFFICE JAPANESE GOVERNMENT page 76 C 421 PATENT ABSTRACTS OF JAPAN, unexamined applications, C field, vol. 10, no. 23, January 29, 1986 THE PATENT OFFICE JAPANESE GOVERNMENT page 96 C 325			
IC	ICM C03C017-25			
	ICS C03C017-36	G02B001-10	H01J001-64	H01J029-22
	C09D001-04			

=>

L5 ANSWER 1 OF 28 USPATFULL
 AN 2002:332614 USPATFULL
 TI Sol-gel method for encapsulating molecules
 IN Brinker, C. Jeffrey, Albuquerque, NM, United States
 Ashley, Carol S., Albuquerque, NM, United States
 Bhatia, Rimple, Albuquerque, NM, United States
 Singh, Anup K., San Francisco, CA, United States
 PA Sandia Corporation, Albuquerque, NM, United States (U.S. corporation)
 PI US 6495352 B1 20021217
 AI US 2000-548638 20000413 (9)
 PRAI US 1999-129771P 19990415 (60)
 DT Utility
 FS GRANTED
 LN.CNT 704
 INCL INCLM: 435/176.000
 INCLS: 435/007.930; 435/026.000; 435/028.000; 436/527.000; 436/815.000;
 436/829.000
 NCL NCLM: 435/176.000
 NCLS: 435/007.930; 435/026.000; 435/028.000; 436/527.000; 436/815.000;
 436/829.000
 IC [7]
 ICM: C12N011-14
 ICS: G01N033-552; C12Q001-32; C12Q001-28
 EXF 435/7.93; 435/26; 435/28; 435/176; 436/527; 436/815; 436/829
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 5 OF 28 USPATFULL
 AN 2002:10777 USPATFULL
 TI Nanoparticulate titanium dioxide coatings, and processes for the
 production and use thereof
 IN Sherman, Jonathan, Franklin, TN, UNITED STATES
 PI AI 20020117
 AI 200001213 (9)
 PRAI US 2000-736738
 US 2000-216937P
 US 2000-0002
 US 2000-202033P
 US 2000-000002
 US 2000-188761P
 US 1999-170509P
 DT Utility
 FS APPLICATION
 LN.CNT 2102
 INCL INCLM: 106/436.000
 NCLM: 106/436.000
 IC [7]
 ICM: C09C001-36
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.